

RF Power MOSFET Transistor 20W, 100-500 MHz, 28V

M/A-COM Products
Released; RoHS Compliant

Features

- N-channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I_{DS}	2.8	A
Power Dissipation	P_D	53	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Thermal Resistance	θ_{JC}	3.3	°C/W

TYPICAL DEVICE IMPEDANCES

F (MHz)	Z_{IN} (Ω)	Z_{LOAD} (Ω)
100	9.5-j60.0	4.0+j68.0
300	5.0-j35.0	40.0+j48.0
500	2.0-j22.0	36.0+j34.0
$V_{DD}=28V$, $I_{DQ}=200$ mA, $P_{OUT}=20.0$ W		

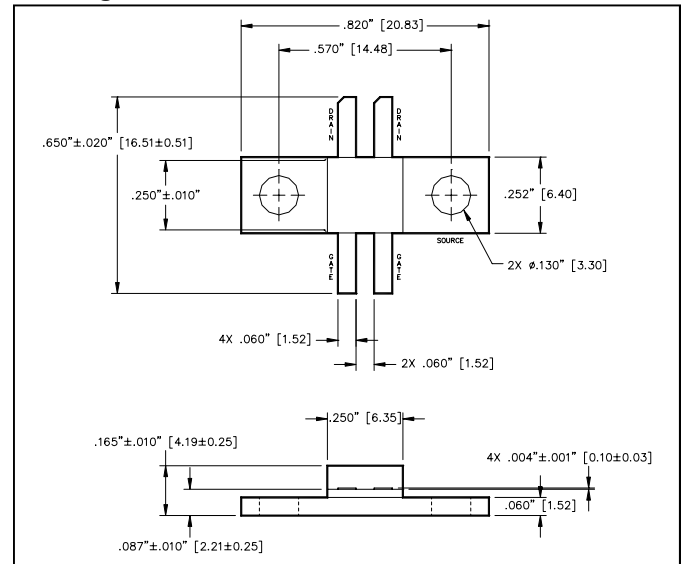
Z_{IN} is the series equivalent input impedance of the device from gate to source.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

ELECTRICAL CHARACTERISTICS AT 25°C

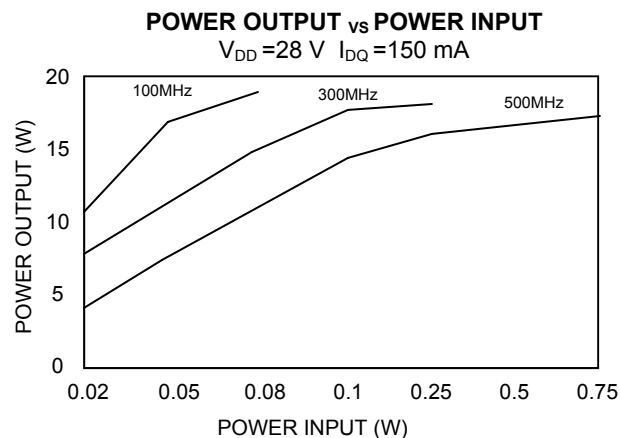
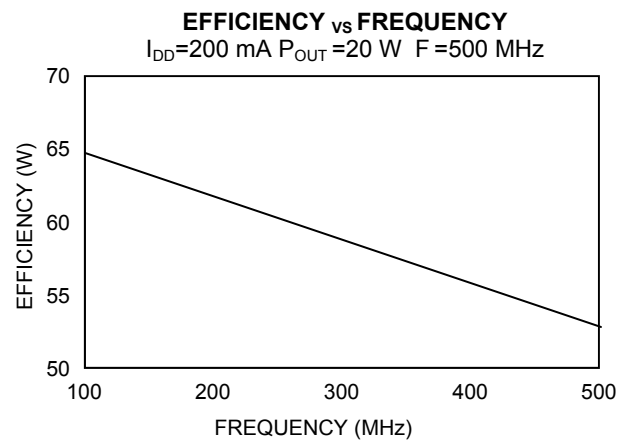
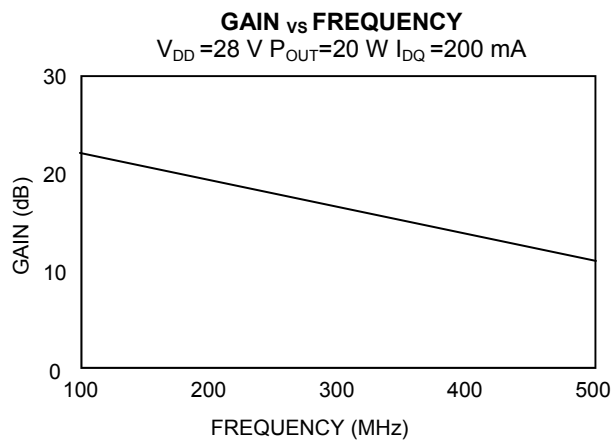
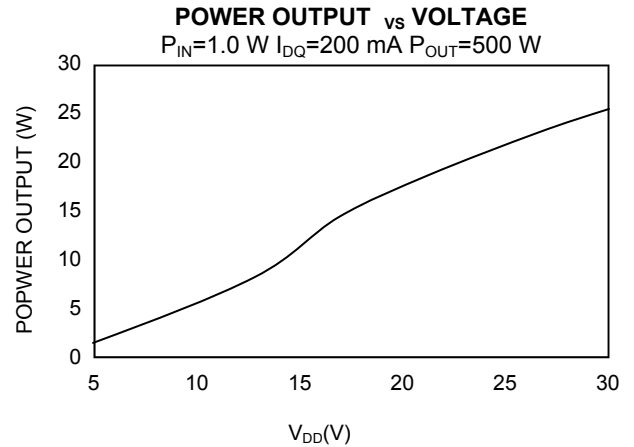
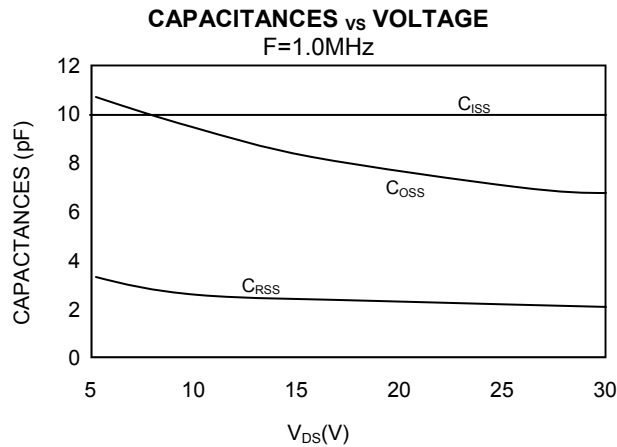
Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	65	-	V	$V_{GS} = 0.0$ V, $I_{DS} = 4.0$ mA
Drain-Source Leakage Current	I_{DSS}	-	2.0	mA	$V_{GS} = 28.0$ V, $V_{DS} = 0.0$ V
Gate-Source Leakage Current	I_{GSS}	-	2.0	μ A	$V_{GS} = 20.0$ V, $V_{DS} = 0.0$ V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS} = 10.0$ V, $I_{DS} = 200.0$ mA
Forward Transconductance	G_M	.160	-	S	$V_{DS} = 10.0$ V, $I_{DS} = 200.0$ mA, $\Delta V_{GS} = 1.0$ V, 80 μ s Pulse
Input Capacitance	C_{ISS}	-	14	pF	$V_{DS} = 28.0$ V, $F = 1.0$ MHz
Output Capacitance	C_{OSS}	-	10	pF	$V_{DS} = 28.0$ V, $F = 1.0$ MHz
Reverse Capacitance	C_{RSS}	-	4.8	pF	$V_{DS} = 28.0$ V, $F = 1.0$ MHz
Power Gain	G_P	10	-	dB	$V_{DD} = 28.0$ V, $I_{DQ} = 200.0$ mA, $P_{OUT} = 20.0$ W $F = 500$ MHz
Drain Efficiency	η_D	50	-	%	$V_{DD} = 28.0$ V, $I_{DQ} = 200.0$ mA, $P_{OUT} = 20.0$ W $F = 500$ MHz
Load Mismatch Tolerance	VSWR-T	-	20:1	-	$V_{DD} = 28.0$ V, $I_{DQ} = 200.0$ mA, $P_{OUT} = 20.0$ W $F = 500$ MHz

Package Outline



UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES $\pm .005$ " [MILLIMETERS ± 0.13 mm]

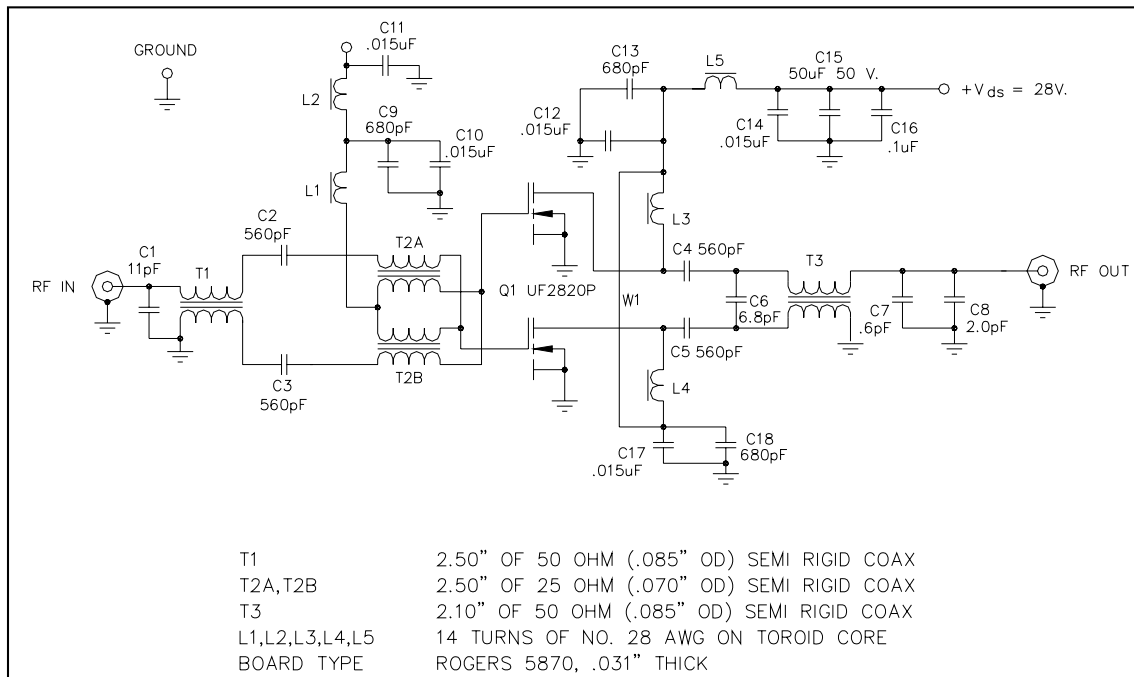
Typical Broadband Performance Curves



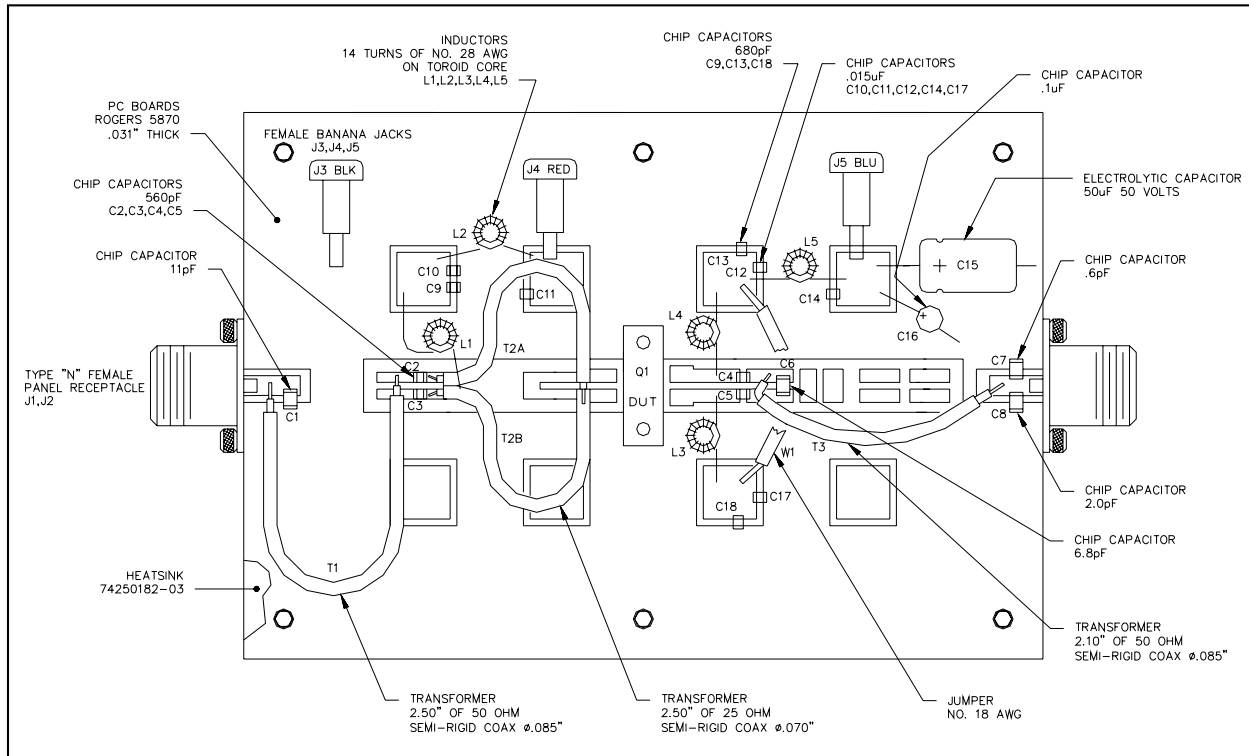
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